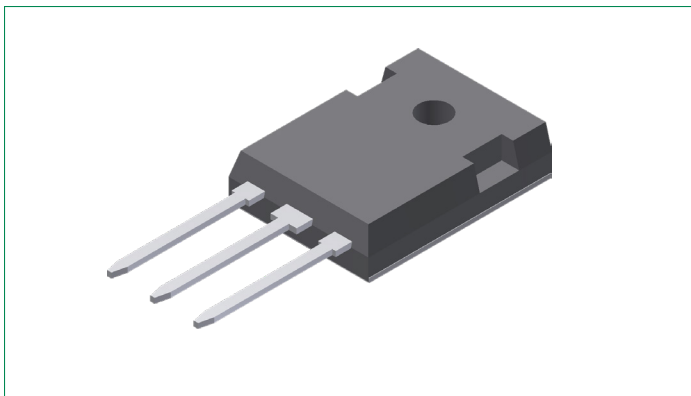


DSA90C200HB

200 V, 2 x 45 A Schottky Diode

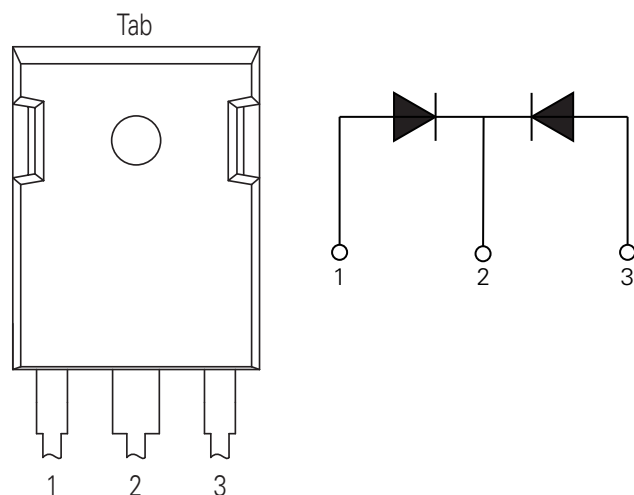
RoHS



Features:

- Very low V_F
- Extremely low switching losses
- Low I_{RM} values
- Improved thermal behavior
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- RoHS compliant
- Epoxy meets UL 94V-0

Pinout Diagram (TO-247)



1: Anode; **2:** Cathode ; **3:** Anode; **tab:** Cathode

Applications:

- Rectifiers in Switch Mode Power Supplies (SMPS)
- Free wheeling diode in low voltage converters

Product Summary

Characteristic	Value	Unit
V_{RRM}	200	V
I_{FAV}	2 x 45	A
V_F	0.78	V

Maximum Ratings

Symbol	Characteristics	Condition	Max.	Units
V_{RSM}	Maximum Non-repetitive Reverse Blocking Voltage	$T_{VJ} = 25^{\circ}\text{C}$	200	V
V_{RRM}	Maximum Repetitive Reverse Blocking Voltage	$T_{VJ} = 25^{\circ}\text{C}$	200	V
I_{RMS}	RMS Current	per terminal	70	A
$I_{R(max)}$	Reverse Current	$V_R = 200\text{ V}, T_{VJM} = 25^{\circ}\text{C}$	1.1	mA
		$V_R = 200\text{ V}, T_{VJM} = 125^{\circ}\text{C}$	5	
$I_{FAV(max)}$	Average Forward Current Rectangular $d = 0.5$	$T_C = 148^{\circ}\text{C}, T_{VJM} = 175^{\circ}\text{C}$	45	A
$I_{FSM(max)}$	Maximum Forward Surge Current (Half Sine)	$t = 10\text{ ms}, (50\text{ Hz}), T_{VJM} = 45^{\circ}\text{C}$	650	A
$P_{tot(max)}$	Total Power Dissipation	$T_C = 25^{\circ}\text{C}$	215	W
T_{VJ}	Virtual Junction Temperature	–	-55 to +175	$^{\circ}\text{C}$
T_{op}	Operating Temperature	–	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics

Symbol	Characteristics	Conditions	Specification	Units
$V_{F(max)}$	Forward Voltage Drop	$I_F = 45\text{ A}; \text{Pulse}, T_{VJM} = 25^{\circ}\text{C}$	0.91	V
		$I_F = 90\text{ A}; \text{Pulse}, T_{VJM} = 25^{\circ}\text{C}$	1.03	
		$I_F = 45\text{ A}; \text{Pulse}, T_{VJM} = 125^{\circ}\text{C}$	0.78	
		$I_F = 90\text{ A}; \text{Pulse}, T_{VJM} = 125^{\circ}\text{C}$	0.93	
$V_{F0(max)}$	Threshold Voltage	$T_{VJM} = 175^{\circ}\text{C}$	0.57	V
$r_{F(max)}$	Slope Resistance		3.2	$\text{m}\Omega$
$C_{J(typ)}$	Junction Capacitance	$V_R = 5\text{ V}, T_{VJM} = 25^{\circ}\text{C}, f = 1\text{ MHz}$	800	pF

Thermal Specifications

Symbol	Characteristics	Condition	Specification	Units
$R_{thJC(max)}$	Thermal Resistance Junction to Case	–	0.7	K/W
$R_{thCH(typ)}$	Thermal Resistance Case to Heat Sink	–	0.3	K/W

Characteristic Curves

Figure 1. Maximum Forward Voltage Drop Characteristics

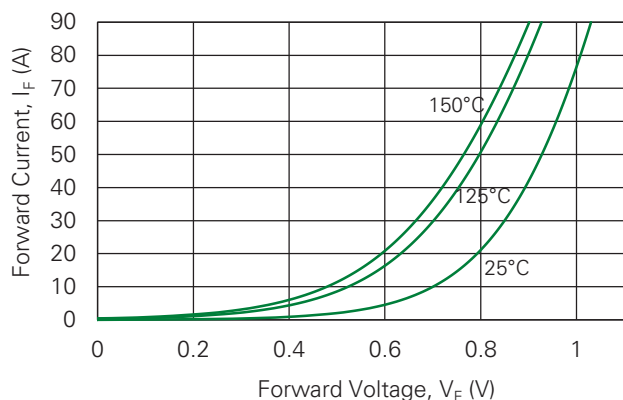


Figure 2. Typical Reverse Current vs. Reverse Voltage

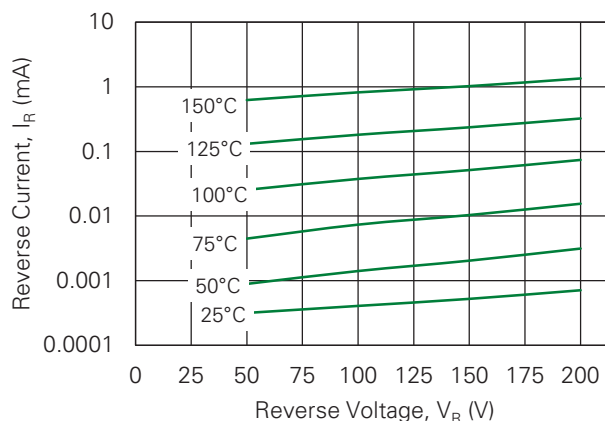


Figure 3. Typical Junction Capacitance vs. Reverse Voltage

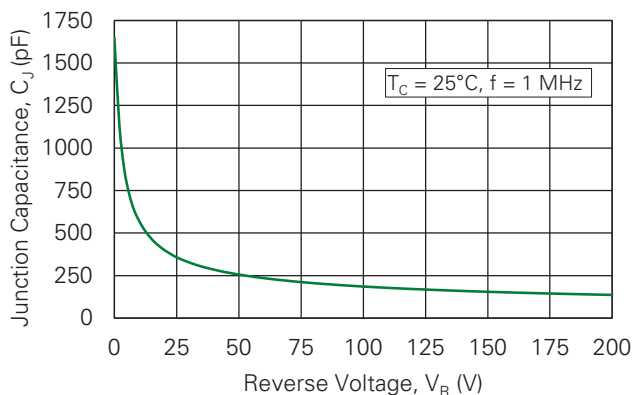


Figure 4. Average Forward Current vs. Case Temperature

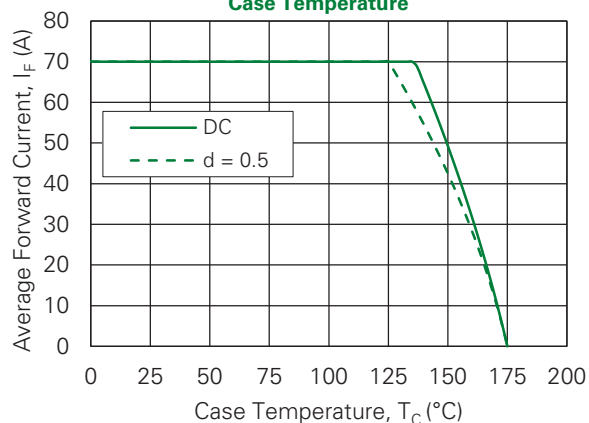


Figure 5. Forward Power Loss Characteristics

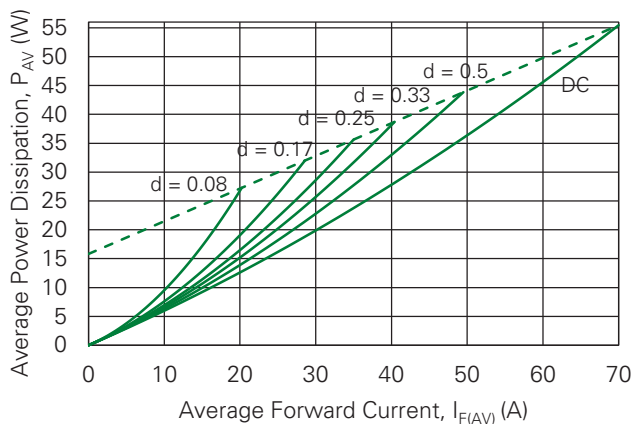


Figure 6. Transient Thermal Impedance

